

BC639_J35Z Datasheet



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DiGi Electronics Part Number BC639_J35Z-DG

Manufacturer onsemi

Manufacturer Product Number BC639_J35Z

Description TRANS NPN 80V 1A T092-3

Detailed Description Bipolar (BJT) Transistor NPN 80 V 1 A 100MHz 1 W T

hrough Hole TO-92-3



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BC639

Purchase and inquiry

Manufacturer:
onsemi
Product Status:
Obsolete
Current - Collector (Ic) (Max):
1 A
Vce Saturation (Max) @ lb, lc:
500mV @ 50mA, 500mA
DC Current Gain (hFE) (Min) @ Ic, Vce:
40 @ 150mA, 2V
Frequency - Transition:
100MHz
Mounting Type:
Through Hole
Supplier Device Package:
TO-92-3

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0075



BC635/637/639

Switching and Amplifier Applications • Complement to BC636/638/640



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CER} Collector-Emitter Voltage at R_{BE} =1KΩ			
02.1	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
V _{CES}	Collector-Emitter Voltage		
	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
V _{CEO}	Collector-Emitter Voltage		
	: BC635	45	V
	: BC637	60	V
	: BC639	80	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	1	А
I _{CP}	Peak Collector Current	1.5	А
I _B	Base Current	100	mA
P _C	Collector Power Dissipation	1	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 ~ 150	°C

PW=5ms, Duty Cycle=10%

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA, I _B =0				
	: BC635	_	45			V
	: BC637		60			V
	: BC639		80			V
I _{CBO}	Collector Cut-off Current	V_{CB} =30V, I_E =0			0.1	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB}=5V$, $I_{C}=0$			0.1	μΑ
h _{FE1}	DC Current Gain : All	V _{CE} =2V, I _C =5mA	25			
h _{FE2}	: BC635	V _{CE} =2V, I _C =150mA	40		250	
	: BC637/BC639		40		160	
h_{FE3}	: All	V _{CE} =2V, I _C =500mA	25			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =500mA, I _B =50mA			0.5	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =2V, I _C =500mA			1	V
f _T	Current Gain Bandwidth Product	V _{CE} =5V, I _C =10mA, f=50MHz		100		MHz

Typical Characteristics

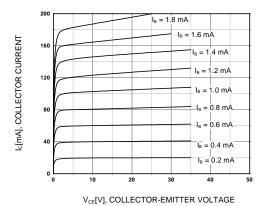


Figure 1. Static Characteristic

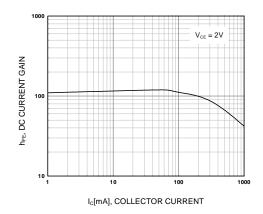


Figure 2. DC current Gain

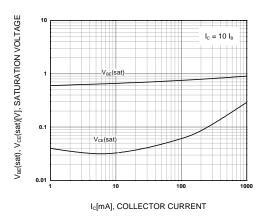


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

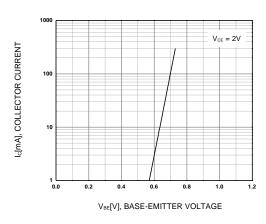


Figure 4. Base-Emitter On Voltage

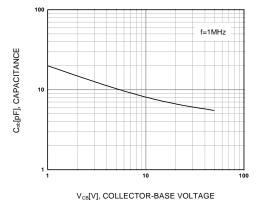
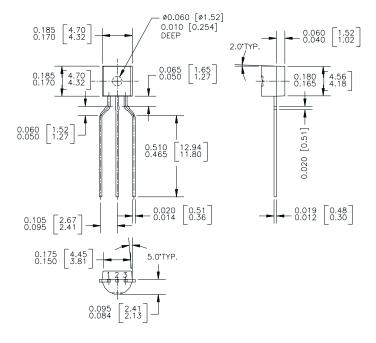


Figure 5. Collector Output Capacitance

Package Dimensions

TO-92



Dimensions in Millimeters

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Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET [®]
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